

Amendment to the claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of claims:

Claim 1 (currently amended): A semiconductor device comprising:

a common substrate;

an SRAM device implemented on the common substrate and isolated by an STI isolation structure ~~a first isolation technique~~; and

a flash EPROM device implemented on the common substrate and isolated by a LOCOS second isolation structure technique,

wherein the STI first isolation structure technique and the LOCOS second isolation structure technique are ~~different and~~ implemented non-concurrently.

Claims 2-3 (canceled)

Claim 4 (original): The semiconductor device according to claim 1 wherein the SRAM device is coupled to the flash EPROM device for transmitting signals between the SRAM device and the flash EPROM device.

Claim 5 (currently amended): A system containing ~~for allowing~~ different types of isolation structures, the system techniques during fabrication of a semiconductor device, comprising:

a common substrate having a first portion including an STI ~~on which a first isolation structure technique is implemented during processing~~ and a second portion including a LOCOS ~~on which a second isolation structure technique is implemented during processing~~, wherein the STI first isolation structure technique and the LOCOS second isolation structure technique are ~~different and~~ implemented non-concurrently;

an SRAM device ~~implemented~~ on the first portion of the substrate; and

a flash EPROM device ~~implemented~~ on the second portion of the substrate.

Claim 6 (original): The system according to claim 5 wherein the SRAM device is coupled to the flash EPROM device for transmitting signals between the SRAM device and the flash EPROM device.

Claims 7-8 (canceled)

Claim 9 (currently amended): A semiconductor device comprising:

a common substrate having a first portion including on which an STI isolation structure technique is implemented during processing and a second portion including on which a LOCOS isolation structure technique is implemented during processing, wherein the STI isolation structure technique and the LOCOS isolation structure technique are implemented non-concurrently;

an SRAM device implemented on the first portion of the substrate; and

a flash EPROM device implemented on the second portion of the substrate.

Claim 10 (original): The semiconductor device according to claim 9 wherein the SRAM device is coupled to the flash EPROM device for transmitting signals between the SRAM device and the flash EPROM device.

Claims 11-17 (previously canceled)

Claim 18 (currently amended): A semiconductor device, comprising:

a common substrate;

a first portion region formed on the common substrate, the first portion region comprising an SRAM device over a first single device layer, the first single device layer comprising a first active region[[,]] and a first isolation region having an STI ~~a first isolation structure formed of a first material, the SRAM device overlying the first active region, the first active region isolated by the first isolation structure;~~ and

a second portion region formed on the common substrate, the second portion region comprising a flash EPROM device over a second single device layer, the second single device layer comprising [[,]] a second active region[[,]] and a second isolation region having a LOCOS ~~second isolation structure formed of a second material, the flash EPROM device overlying the second active region, the second active region isolated by the second isolation structure,~~

~~wherein the first isolation structure is contiguous to and different from the second isolation structure.~~

Claims 19-20 (canceled)

Claim 21 (currently amended): The semiconductor device of claim 18, wherein the first single device layer material comprises an insulating oxide.

Claim 22 (currently amended): The semiconductor device of claim 18, wherein the second single device layer material comprises an insulating oxide.

Claim 23 (currently amended): A semiconductor device comprising:

a common substrate;

an SRAM device implemented on the common substrate and formed over a first active region on a first isolated structure including an STI isolation structure; and

a flash EPROM device implemented on the common substrate and formed over a second active region on a second isolated structure including a LOCOS isolation structure, the second isolated structure having an outer a first portion extending a first depth into the substrate and an inner a second portion containing including the second active region and

extending a second depth into the substrate, the first depth larger than the second depth[[,]]

~~wherein the first isolated structure and the second isolated structure are different.~~

Claim 24 (previously presented): The semiconductor device of claim 23, wherein the first isolated structure and the second isolated structure are contiguous.

Claim 25 (previously presented): The semiconductor device of claim 23, wherein the first isolated structure and the second isolated structure both comprise an oxide material.

Claim 26 (currently amended): A system containing a semiconductor device having a plurality of isolated structures, the system comprising:

a common substrate having a first area portion including an STI on which a first isolation structure technique is implemented during processing and a second area portion including a LOCOS on which a second isolation structure technique is implemented during processing, the second area portion having an outer portion a first segment extending a first depth into the substrate and an inner portion a second segment containing including an active region extending a second depth into the substrate, wherein the first depth is larger than the second depth and further wherein the first isolation technique and the second isolation technique are different;

an SRAM device implemented on the first area portion of the substrate; and

a flash EPROM device implemented on the second area portion of the substrate.

Claim 27 (currently amended): The system of claim 26, wherein the first area portion and the second area portion are contiguous.

Claim 28 (currently amended): The system of claim 27, wherein the first area portion and the second area portion both comprise an oxide material.